

EYP-DFB-1083-00080-1500-BFW01-0000

Revision 0.51

26.03.2015

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DISTRIBUTED FEEDBACK LASER

GaAs Semiconductor Laser Diode with integrated grating structure



General Product Information

| Product | Application |
|---|--------------|
| 1083 nm DFB Laser with hermetic Butterfly Housing | Spectroscopy |
| Monitor Diode, Thermoelectric Cooler and Thermistor | Metrology |
| Collimated beam | Magnetometer |
| ROHS compliant | |



Absolute Maximum Ratings

| | Symbol | Unit | min | typ | max |
|---------------------------------------|-----------|------|-----|-----|-----|
| Storage Temperature | T_S | °C | -40 | | 85 |
| Operational Temperature at Case | T_C | °C | -40 | | 85 |
| Operational Temperature at Laser Chip | T_{LD} | °C | 10 | | 50 |
| Forward Current | I_F | mA | | | 200 |
| Reverse Voltage | V_R | V | | | 2 |
| Output Power | P_{opt} | mW | | | 90 |
| TEC Current | I_{TEC} | A | | | 1.1 |
| TEC Voltage | V_{TEC} | V | | | 2.8 |

Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device.

Recommended Operational Conditions

| | Symbol | Unit | min | typ | max |
|---------------------------------------|-----------|------|-----|-----|-----|
| Operational Temperature at Case | T_C | °C | -20 | | 65 |
| Operational Temperature at Laser Chip | T_{LD} | °C | 15 | | 40 |
| Forward Current | I_F | mA | | | 190 |
| Output Power | P_{opt} | mW | 20 | | 80 |

Measurement Conditions / Comments

measured by integrated Thermistor

Characteristics at $T_{LD} = 25\text{ °C}$ at Begin Of Life

| Parameter | Symbol | Unit | min | typ | max |
|---------------------------------------|-----------------|---------|------|-------|------|
| Center Wavelength | λ_C | nm | 1082 | 1083 | 1084 |
| Spectral Width (FWHM) | $\Delta\nu$ | MHz | | 2 | |
| Temperature Coefficient of Wavelength | $d\lambda / dT$ | nm / K | | 0.06 | |
| Current Coefficient of Wavelength | $d\lambda / dI$ | nm / mA | | 0.003 | |
| Output Power @ $I_F = 190\text{ mA}$ | P_{opt} | mW | 80 | | |

Measurement Conditions / Comments

see images on page 4

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Characteristics at $T_{amb} 25\text{ °C}$ at Begin Of Life cont'd

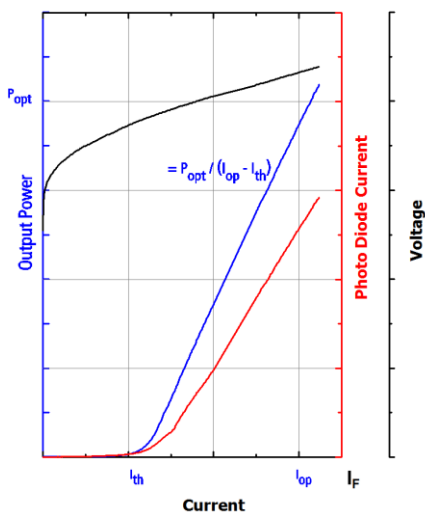
| Parameter | Symbol | Unit | min | typ | max |
|--|------------------|-------|-----|-----|-----|
| Slope Efficiency | η | W / A | 0.6 | 0.8 | 1.0 |
| Threshold Current | I_{th} | mA | | | 70 |
| Divergence parallel ($1/e^2$) | $\Theta_{ }$ | ° | | 0.1 | |
| Divergence perpendicular ($1/e^2$) | Θ_{\perp} | ° | | 0.1 | |
| Beam Diameter ($1/e^2$) | $d_{ }$ | mm | | 1.0 | 1.2 |
| Beam Diameter ($1/e^2$) | d_{\perp} | mm | | 0.8 | 1.2 |
| Degree of Polarization | DOP | % | | 90 | |
| Sidemode Supression Ratio | SMSR | dB | 30 | 50 | |
| Mode-hop free Operating Range (SMSR > 30 dB) | | | | | |
| ▶ Variant 0 | T_{LD} | ° C | | 25 | |
| | P_{opt} | mW | | 80 | |
| ▶ Variant 2 | T_{LD} | ° C | 15 | | 40 |
| | P_{opt} | mW | 20 | | 80 |

Measurement Conditions / Comments

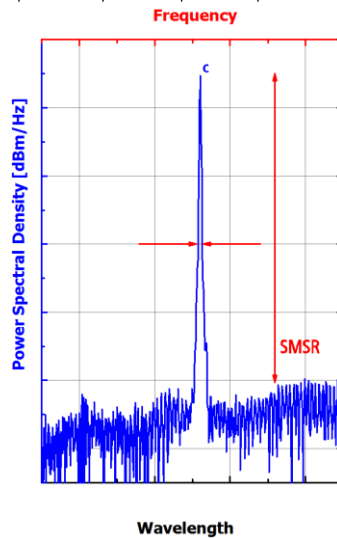
parallel to the base plate of the housing (see p. 3)
 perpendicular to base plate of the housing (see p. 3)
 parallel to the base plate of the housing (see p. 3)
 perpendicular to base plate of the housing (see p. 3)
 $P_{opt} = 80\text{ mW}$; E field parallel to the base plate
 $P_{opt} = 80\text{ mW}$
 see order code scheme on p. 5

Typical Measurement Results

Output Power vs. Current



Spectra at Specified Optical Output Power



Pictures and the illustrative graphs (on the left hand side) provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract.

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Monitor Diode

| Parameter | Symbol | Unit | min | typ | max |
|-------------------------------|---------------------------------|------------------|-----|-----|-----|
| Monitor Detector Responsivity | $I_{\text{mon}}/P_{\text{opt}}$ | $\mu\text{A/mW}$ | | tbd | |

Measurement Conditions / Comments

Reverse Voltage $U_{R\text{ MD}} = 5\text{ V}$

Thermoelectric Cooler

| Parameter | Symbol | Unit | min | typ | max |
|--|-------------------|------|-----|-----|-----|
| Current | I_{TEC} | A | | 0.4 | |
| Voltage | U_{TEC} | V | | 0.8 | |
| Power Dissipation (total loss at case) | P_{loss} | W | | 0.4 | |
| Temperature Difference | ΔT | K | | | 50 |

Measurement Conditions / Comments

$P_{\text{opt}} = 80\text{ mW}$, $\Delta T = 20\text{ K}$

$P_{\text{opt}} = 80\text{ mW}$, $\Delta T = 20\text{ K}$

$P_{\text{opt}} = 80\text{ mW}$, $\Delta T = 20\text{ K}$

$P_{\text{opt}} = 80\text{ mW}$, $\Delta T = |T_{\text{case}} - T_{\text{LD}}|$

Thermistor (Standard NTC Type)

| Parameter | Symbol | Unit | min | typ | max |
|------------------|---------|-----------|-----|------|-----|
| Resistance | R | $k\Omega$ | | 10 | |
| Beta Coefficient | β | | | 3892 | |

Measurement Conditions / Comments

$T = 0^\circ \dots 50^\circ\text{ C}$

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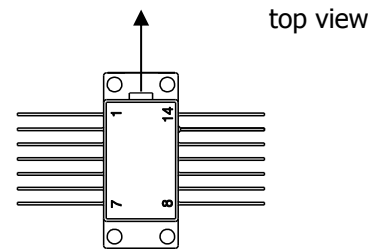
Package Dimensions

| Parameter | Symbol | Unit | min | typ | max |
|----------------|----------|------|-----|-----|-----|
| Emission Plane | h_{EP} | mm | | 4.9 | |

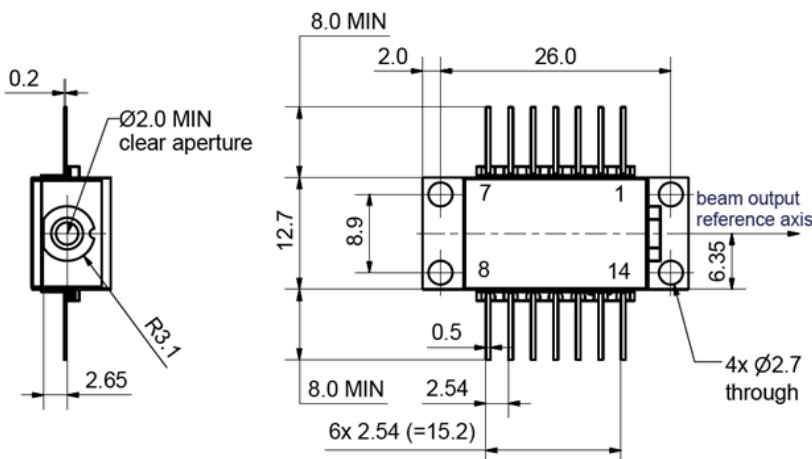
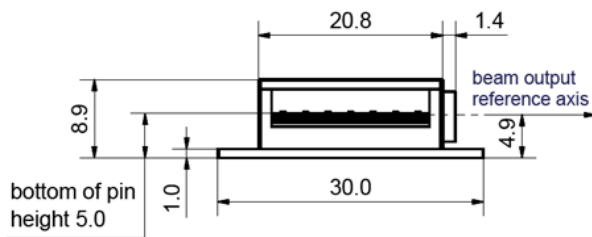
Measurement Conditions / Comments

Package Pinout

| | | | |
|---|---------------------------|----|---------------------------|
| 1 | Thermoelectric Cooler (+) | 14 | Thermoelectric Cooler (-) |
| 2 | Thermistor | 13 | Case |
| 3 | Photodiode (Anode) | 12 | not connected |
| 4 | Photodiode (Cathode) | 11 | Laser Diode (Cathode) |
| 5 | Thermistor | 10 | Laser Diode (Anode) |
| 6 | not connected | 9 | not connected |
| 7 | not connected | 8 | not connected |



Package Drawings



Z13-0000-BFY32-DBR-0000 Vers. 0.92

Polarization:

E field parallel to the base plate

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Order Code Scheme

Mode-hop free Operating Range (Minimum Side Mode Suppression Ratio > 30 dB)

| | | |
|-------------------------------------|---|-------------|
| $P_{opt} = 80 \text{ mW};$ | $T_{LD} = 25 \text{ }^\circ\text{C}$ | (Variant 0) |
| $P_{opt} = 20 \dots 80 \text{ mW};$ | $T_{LD} = 15 \dots 40 \text{ }^\circ\text{C}$ | (Variant 2) |

EYP-DFB-1083-00080-1500-BFW01- 0 0 0 x

0

2

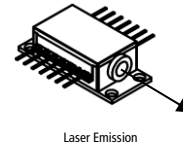
Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

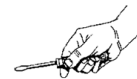
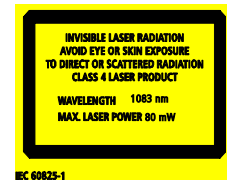
Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.



hersta



Ordering Information:



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Email orders to: sales@xsoptix.com
Fax orders to: 800-878-7282